

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	9.2255	N/A	4.7743
RT2	12.5770	N/A	3.7460
RT3	16.2415	N/A	7.5109
RT4	41.9562	N/A	5.9687
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	219.2622 m	N/A	26.8428 m
CT2	486.6010 u	N/A	231.3888 u
CT3	10.0294 m	N/A	2.1484 m
CT4	1.9025	N/A	1.9186 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	14.1958	N/A	7.5008
RF2	18.8676	N/A	9.4976
RF3	16.2142	N/A	3.8843
RF4	30.7225	N/A	1.1173
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	478.0101 u	N/A	230.0347 u
CF2	11.3892 m	N/A	1.1954 m
CF3	666.7729 m	N/A	7.4209 m
CF4	2.0625	N/A	329.4700 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

